

Day : Sunday  
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# PALM INTRANET

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Amend** [Spl-New](#) [Spl-Amend](#) [Accl-New](#) [Accl-Amend](#) [Rejected](#)

## Regular Amended Cases

(WARNING: Data Security and Confidentiality Restriction Apply)

Name : **SCHILLINGER, LAURA**

Examiner Number : **74721**

Group Art Unit : **2813**

Regular Amended Cases :**52**

Application #	Fwd-to-Exmr	Status	Loc	ChgTo Loc	Class	SubClass	Mo-Old	Unavail	Type	Gau	Title
09/942445 IFW IMAGE	01/10/2007	121	e	e	438	122.000	2+	-	-		SEMICOND DEVICE AN MANUFAC' METHOD T
10/681507 IFW IMAGE	02/07/2007	71	e	e	438	381.000	2+	-	-		ELECTRICAL ISOLATED IN ACTIVE
11/086446 IFW IMAGE	02/23/2007	71	e	e	257	079.000	2+	-	-		SEMICOND DEVICE AN MANUFAC' METHOD T
10/276306 IFW IMAGE	02/24/2007	71	e	e	438	458.000	2+	-	-		EMBRITTLING SUBSTRATE METHOD FOR MAKING SEMICONDUCTOR
10/485046 IFW IMAGE	02/25/2007	71	e	e	257	678.000	2+	-	-		VERTICAL INTEGRATION
10/994265 IFW IMAGE	02/27/2007	71	e	e	438	149.000	2+	-	-		THIN FILM TRANSISTOR METHOD OF MANUFACTURING THE SAME
10/986936 IFW IMAGE	03/03/2007	71	e	e	438	795.000	2+	-	-		LASER AND APPARATUS FOR ANNEALING OF SEMICONDUCTOR THIN FILM THE SAME

<u>10/992596</u> IFW IMAGE	03/06/2007	71	e	e	438	123.000	2+	-	-	METHOD F FABRICATI SEMICOND DEVICES U STRAINED BEARING M
<u>09/845336</u> IFW IMAGE	03/13/2007	71	e	e	257	079.000	2+	-	-	GROUP III N COMPOUND SEMICOND LIGHT-EMI DEVICE
<u>10/706912</u> IFW IMAGE	03/13/2007	71	e	e	438	048.000	2+	-	-	ELECTRON DEVICES A PRODUCTIO METHODS
<u>10/990711</u> IFW IMAGE	03/19/2007	71	e	e	438	527.000	2+	-	-	SYSTEMS A METHODS INTEGRATI HETEROGE CIRCUIT DI
<u>10/831617</u> IFW IMAGE	03/20/2007	71	e	e	438	562.000	2+	-	-	PROCESS O FABRICATI SEMICOND DEVICE
<u>11/223069</u> IFW IMAGE	03/20/2007	71	e	e	438	382.000	2+	-	-	ELECTRICA PROGRAMM POLYSILIC WITH MUL LEVEL RES AND PROG
<u>10/899833</u> IFW IMAGE	03/23/2007	71	e	e	438	123.000	2+	-	-	SEMICOND PROCESSIN METHODS FORMING INTEGRATI CIRCUITRY
<u>11/204418</u> IFW IMAGE	03/23/2007	71	e	e	438	197.000	2+	-	-	PROCESS F ULTRA-THI SOI DEVICE INCORPOR. SILICON TI ARTICLE M THEREBY
<u>10/210109</u> IFW IMAGE	03/24/2007	71	e	e	438	158.000	2+	-	-	PHOTOLITH METHOD F FABRICATI FILM

10/612333 IFW IMAGE	03/27/2007	71	e	e	438	123.000	2	-	-	SELECTIVE POLYSILIC GROWTH
10/987135 IFW IMAGE	03/30/2007	71	e	e	438	028.000	2	-	-	METHODS PROCESSIN SEMICOND WAFER BA HAVING LI EMITTING (LEDS) THE
10/772585 IFW IMAGE	04/05/2007	71	e	e	257	363.000	2	-	-	SEMICOND DEVICE
10/799626 IFW IMAGE	04/13/2007	71	e	e	438	795.000	1+	-	-	LASER IRR APPARATU IRRADIATI METHOD, A METHOD F MANUFAC SEMICOND DEVICE
11/001575 IFW IMAGE	04/18/2007	71	e	e	438	458.000	1+	-	-	SUBSTRAT ATTACHIN
10/755001 IFW IMAGE	04/23/2007	71	e	e	438	643.000	1+	-	-	METHODS FORMING MATERIAL COMPRISIN TUNGSTEN NITROGEN. METHODS FORMING CAPACITO
10/818155 IFW IMAGE	04/23/2007	121	e	e	438	197.000	1+	-	-	DISPOSABI PROCESS F EFFECT TR FABRICATI
11/217033 IFW IMAGE	04/23/2007	71	e	e	257	296.000	1+	-	-	SEMICOND PROCESSIN METHODS FORMING TRANSISTC SEMICOND PROCESSIN METHODS FORMING I RANDOM A MEMORY C

										AND RELA INTEGRATI CIRCUITRY
<u>11/031316</u> IFW IMAGE	04/24/2007	71	e	e	438	112.000	1	-	-	METHOD F FORMING A FLEXIBLE I FOIL SUBST DISPLAY
<u>11/067186</u> IFW IMAGE	04/24/2007	71	e	e	438	123.000	1	-	-	HIGH PERF FET DEVICE METHODS
<u>10/626620</u> IFW IMAGE	04/26/2007	71	e	e	257	314.000	1	-	-	METHOD T AN OXIDE ALONG GA EDGE, WHI SPACE FOR BEGINS WI OXIDE LIN SURROUND STACK
<u>11/003275</u> IFW IMAGE	05/01/2007	77	e	e	438	279.000	1	-	-	METHODS FORMING INTEGRATI CIRCUITRY METHODS FORMING N CIRCUITRY METHODS FORMING P EFFECT TRANSISTC
<u>11/201504</u> IFW IMAGE	05/02/2007	71	e	e	438	143.000	1	-	-	CAPACITO SEMICOND DEVICE HA DUAL DIEL FILM STRU AND METH FABRICATI SAME
<u>10/973161</u> IFW IMAGE	05/07/2007	71	e	e	438	105.000	1	-	-	METHODS FORMING A CONDUCTI DIAMOND STRUCTUR FORMED T]
<u>11/275850</u> IFW	05/08/2007	71	e	e	438	151.000	-1	-	-	SEMICOND DEVICE AN METHOD O

IMAGE										MANUFAC THE SAME
09/685698 IFW IMAGE	05/10/2007	71	e	e	257	072.000	-1	-	-	EL DISPLAY AND A METAL MANUFACTURE SAME
10/194506 IFW IMAGE	05/10/2007	71	e	e	438	151.000	-1	-	-	PROCESS FOR ULTRA-THIN SOI DEVICE INCORPORATING SILICON TITANIUM ARTICLE MANUFACTURED THEREBY
11/544358 IFW IMAGE	05/10/2007	71	e	e	257	072.000	-1	-	-	EL DISPLAY AND A METAL MANUFACTURE THE SAME
10/472446 IFW IMAGE	05/15/2007	71	e	e	438	478.000	-1	-	-	METHOD FOR MANUFACTURING ZNTE COMBINATION SEMICONDUCTOR SINGLE CRISTAL ZNTE COMBINATION SEMICONDUCTOR SINGLE CRISTAL AND SEMICONDUCTOR DEVICE
11/057246 IFW IMAGE	05/15/2007	71	e	e	438	123.000	-1	-	-	METHOD OF FORMING SEMI NITRIDE FILM METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
11/296164 IFW IMAGE	05/15/2007	71	e	e	438	123.000	-1	-	-	APPLICATION OF DIFFERENT ISOLATION FOR LOGIC EMBEDDED
10/999270 IFW IMAGE	05/16/2007	71	e	e	438	197.000	-1	-	-	PHOSPHOR FREE PROCESS POLYSILICON DEFINITION
										METHODS OF FORMING FIELD EFFECT

<u>11/000809</u> IFW IMAGE	05/16/2007	71	e	e	438	300.000	-1	-	-	TRANSISTOR METHODS OF FORMING FIELD EFFECT TRANSIS- TORS AND LINES
<u>11/377054</u> IFW IMAGE	05/17/2007	71	e	e	438	597.000	-1	-	-	SEMICONDUCTOR CONSTRUCTION
<u>10/419076</u> IFW IMAGE	05/23/2007	71	e	e	438	424.000	-1	-	-	METHOD OF PLANARIZING SURFACE OF SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE MANUFACTURE ACCORDING TO SAME
<u>10/982115</u> IFW IMAGE	05/24/2007	71	e	e	438	197.000	-1	-	-	ADVANCED DISPOSABLE PROCESS BY TEMPERATURE STRESS NITRIDE FILM FOR CMOS TECHNOLOGY
<u>10/019407</u> IFW IMAGE	05/25/2007	71	e	e	438	160.000	-1	-	-	POLYSILICON SEMICONDUCTOR THIN FILM SUBSTRATE METHOD FOR PRODUCING SAME, SEMICONDUCTOR DEVICE, AND ELECTRON DETECTOR
<u>10/784436</u> IFW IMAGE	06/04/2007	71	e	e	438	106.000	-1	-	-	THROUGH- CONDUCTING SEMICONDUCTOR SUBSTRATE METHOD AND SYSTEM FOR MAKING SAME
<u>10/982375</u> IFW	06/04/2007	71	e	e	438	400.000	-1	-	-	METHOD WITH MECHANICALLY STRAINED FOR ENHANCING SPEED OF

IMAGE										INTEGRATI CIRCUITS C DEVICES
11/004836 IFW IMAGE	06/04/2007	77	e	e	438	197.000	-1	-	-	SEMICOND DEVICE AN METHOD F FABRICATI SAME
11/216915 IFW IMAGE	06/05/2007	71	e	e	257	510.000	-1	-	-	SEMICOND PROCESSIN METHODS FORMING TRANSISTO SEMICOND PROCESSIN METHODS FORMING I RANDOM A MEMORY C AND RELA INTEGRATI CIRCUITRY
10/985666 IFW IMAGE	06/06/2007	71	e	e	438	118.000	-1	-	-	SEMICOND DEVICE MANUFAC METHOD A MANUFAC APPARATU
10/995406 IFW IMAGE	06/07/2007	71	e	e	438	048.000	-1	-	-	METHOD O MANUFAC MEMS DEV
10/996866 IFW IMAGE	06/08/2007	71	e	e	438	300.000	-1	-	-	HIGH PERF FET WITH I SOURCE/DI REGION
10/313686 IFW IMAGE	06/09/2007	71	e	e	438	105.000	-1	-	-	METHODS FORMING A CONDUCTI DIAMOND STRUCTUR FORMED TI
10/890129 IFW IMAGE	06/09/2007	71	e	e	438	123.000	-1	-	-	SEMICOND DEVICE AN MANUFAC METHOD

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